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EXCHANGE COUPLING AND SPIN-FLIP TRANSITION OF $\text{CoFe}_2\text{O}_4/\alpha\text{-Fe}_2\text{O}_3$ BILAYERED FILMS

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ABSTRACT

$\text{CoFe}_2\text{O}_4/\alpha\text{-Fe}_2\text{O}_3$ (ferrimagnetic / antiferromagnetic) bilayered films were prepared on $\alpha\text{-Al}_2\text{O}_3(102)$ single-crystalline substrates by helicon plasma sputtering. A well-crystallized epitaxial $\alpha\text{-Fe}_2\text{O}_3(102)$ layer was formed on the substrate, while CoFe_2O_4 grown on $\alpha\text{-Fe}_2\text{O}_3(102)$ was a polycrystalline layer with a (100)-preferred orientation. The $\alpha\text{-Fe}_2\text{O}_3(102)$ films without CoFe_2O_4 layers clearly showed a spin-flip transition at about 400 K. The spins aligned perpendicular to the film plane at room temperature changed their direction within the film plane above 400 K. However the $\alpha\text{-Fe}_2\text{O}_3$ base layers of $\text{CoFe}_2\text{O}_4/\alpha\text{-Fe}_2\text{O}_3$ bilayered films did not show any spin-flip transition. The CoFe_2O_4 layer on $\alpha\text{-Fe}_2\text{O}_3$ had a large in-plane magnetic anisotropy, while the spin axis of the $\alpha\text{-Fe}_2\text{O}_3(102)$ base layer was directed perpendicular to the film plane. The magnetization of ferrimagnetic CoFe_2O_4 layers was coupled perpendicularly to the spin axis of antiferromagnetic $\alpha\text{-Fe}_2\text{O}_3$ layers due to the exchange coupling at the interface between CoFe_2O_4 and $\alpha\text{-Fe}_2\text{O}_3$.

INTRODUCTION

Exchange coupling at an interface between ferromagnetic (FM) and antiferromagnetic (AFM) layers has received much attention mainly due to the technological applications in such devices as spin-valve sensors. It stabilizes a magnetic direction of the FM layer and functions as a bias field in the magnetic hysteresis loop. Recently, full micromagnetic calculations suggested the existence of the 90° FM - AFM coupling at the interface [1]. However the fundamental origin of exchange coupling between magnetic materials, especially magnetic oxide materials, is still unclear. $\alpha\text{-Fe}_2\text{O}_3$ is one of candidates for the AFM materials fabricated in the spin-valve sensors [2,3]. The spin valves partly consisting of $\alpha\text{-Fe}_2\text{O}_3$ have high thermal stability and large magneto-resistance ratio. By the way, one of the present authors found that epitaxial $\alpha\text{-Fe}_2\text{O}_3(102)$ films on $\alpha\text{-Al}_2\text{O}_3(102)$ had an unique spin-flip transition [4]. The transition takes place at about 400 K, much higher than the Morin transition temperature (260 K) of the bulk crystal. The spin axis lying within a film plane above 400 K turns perpendicular to the film plane below the transition temperature.

There are a few studies on the exchange coupling between oxide materials with the FM/AFM bilayered structure [5]. Most of practical FM oxides are exactly ferrimagnetic. Microscopic spin configurations at the interface between oxide systems could be different from the ones between metallic systems. We prepared well-crystallized $\alpha\text{-Fe}_2\text{O}_3$ and CoFe_2O_4 bilayered films by using helicon plasma sputtering technique [6]. CoFe_2O_4 is a typical ferrimagnetic material with an inverse spinel structure. Structural properties and magnetic interactions between ferrimagnetic CoFe_2O_4 (FM) and $\alpha\text{-Fe}_2\text{O}_3$ (AFM) layers were discussed. If the exchange coupling at the $\text{CoFe}_2\text{O}_4/\alpha\text{-Fe}_2\text{O}_3$ interface was strong enough, magnetic properties of the CoFe_2O_4 layer should be influenced by the spin-flip transition of the $\alpha\text{-Fe}_2\text{O}_3$ layer or vice versa.

EXPERIMENT

Helicon plasma sputtering is a powerful technique to prepare high-quality multilayered films with sharp interfaces [7]. It has some advantages in comparison with conventional rf magnetron sputtering, such as high deposition rate stability and low plasma damage to the film surface. A helicon plasma cathode consists of a conventional rf magnetron cathode and a rf coil for a helicon wave. Fig.1 shows a schematic drawing of the helicon plasma sputtering system we used. Two targets for helicon cathodes were made of sintered $\alpha\text{-Fe}_2\text{O}_3$ and CoO , respectively. The base pressure of the system was 10^{-7} Pa. Before sputter deposition an $\alpha\text{-Al}_2\text{O}_3(102)$ substrate was annealed in vacuum at about 973 K for 1 hour in order to obtain a clean and well-ordered surface. $\alpha\text{-Fe}_2\text{O}_3$ base layers with the thickness of 100 nm were sputtered on the substrate at the substrate temperature of 673 K. CoFe_2O_4 layers with several thicknesses ranging from 25 to 200 nm were then deposited on $\alpha\text{-Fe}_2\text{O}_3$ at 773 K by simultaneous sputtering from both targets, to control the deposition rate ratio between $\alpha\text{-Fe}_2\text{O}_3$ and CoO . The deposited films were characterized by reflection high energy electron diffraction (RHEED), x-ray diffraction (XRD), scanning probe microscopy (SPM), vibrating sample magnetometer (VSM), conversion electron Mössbauer spectroscopy (CEMS), and energy dispersive X-ray spectroscopy (EDS).

RESULTS AND DISCUSSION

Typical XRD and RHEED patterns of $\alpha\text{-Fe}_2\text{O}_3$ films deposited on $\alpha\text{-Al}_2\text{O}_3$ (102) single-crystalline substrates are shown in figs. 2(a) and (b), respectively. Epitaxial relationship between the $\alpha\text{-Fe}_2\text{O}_3$ layer and the $\alpha\text{-Al}_2\text{O}_3$ substrate can clearly be seen in both XRD and RHEED patterns. The XRD pattern had only a reflection from the film indexed as $\alpha\text{-Fe}_2\text{O}_3(204)$ at the side of an intense $\alpha\text{-Al}_2\text{O}_3$ (204) reflection. The sharp streak lines in the RHEED pattern indicated an atomically flat surface of the layer. Both $\alpha\text{-Fe}_2\text{O}_3$ and $\alpha\text{-Al}_2\text{O}_3$ have a corundum structure with a small lattice misfit of +5.8 %. This could be a reason why the well-crystallized and atomically flat $\alpha\text{-Fe}_2\text{O}_3$ layers were epitaxially formed on the $\alpha\text{-Al}_2\text{O}_3$ substrates.

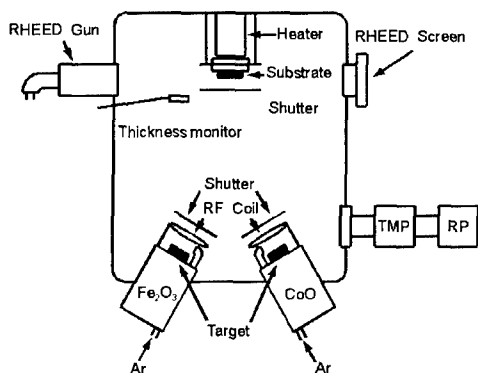


Figure 1. Schematic drawing of helicon plasma sputtering system we used. The helicon cathodes consist of conventional rf magnetron cathodes and rf coils.

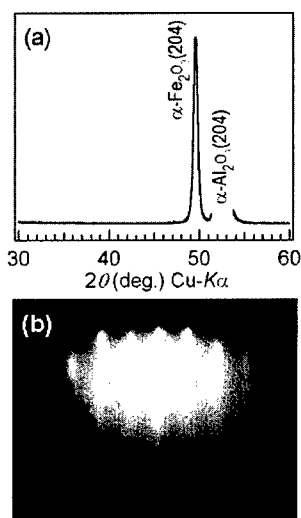


Figure 2. (a) XRD and (b) RHEED patterns of an $\alpha\text{-Fe}_2\text{O}_3$ film deposited on an $\alpha\text{-Al}_2\text{O}_3$ (102) substrate.

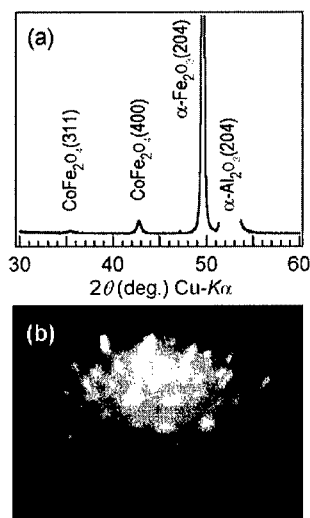


Figure 3. (a) XRD and (b) RHEED patterns of a $\text{CoFe}_2\text{O}_4/\alpha\text{-Fe}_2\text{O}_3$ bilayered film deposited on an $\alpha\text{-Al}_2\text{O}_3$ (102) substrate. Thicknesses of the CoFe_2O_4 and the $\alpha\text{-Fe}_2\text{O}_3$ layers were 200 and 100 nm, respectively.

Figs. 3(a) and (b) are typical XRD and RHEED patterns of $\text{CoFe}_2\text{O}_4/\text{Fe}_2\text{O}_3$ bilayered films, respectively. The XRD pattern of the $\text{CoFe}_2\text{O}_4/\text{Fe}_2\text{O}_3$ bilayered film had two reflections from the CoFe_2O_4 layer indexed as CoFe_2O_4 (311) and (400) in addition to the reflection from the $\alpha\text{-Fe}_2\text{O}_3$ (204) base layer. The relative peak intensity ratio of CoFe_2O_4 (400) to (311) was considerably large, in comparison with that of the CoFe_2O_4 bulk pattern with random orientation [8]. The CoFe_2O_4 layer formed on $\alpha\text{-Fe}_2\text{O}_3$ (102) had strong (100)-preferred orientation. In crystallographic aspects, the $\alpha\text{-Fe}_2\text{O}_3$ (102) surface has a pseudo-square structure though the $\alpha\text{-Fe}_2\text{O}_3$ crystal has hexagonal corundum structure. The CoFe_2O_4 (100) layer with cubic spinel structure could be formed on the $\alpha\text{-Fe}_2\text{O}_3$ (102) base layer. However the lattice misfit between them is very large, about $\sim 17\%$. The RHEED pattern of CoFe_2O_4 on $\alpha\text{-Fe}_2\text{O}_3$ (102) was spotted and complicated. The CoFe_2O_4 layers in bilayered films were poly-crystallized and had (100)-preferred orientation. Moreover, chemical formula of the CoFe_2O_4 layer analyzed by EDS was $\text{Co}_{0.7}\text{Fe}_{2.3}\text{O}_4$.

The spin direction of $\alpha\text{-Fe}_2\text{O}_3$ layers on $\alpha\text{-Al}_2\text{O}_3$ (102) was easily determined by CEMS. The CEMS spectrum of $\alpha\text{-Fe}_2\text{O}_3$ generally exhibited six lines due to the nuclear Zeeman splitting from a large internal magnetic field. Relative peak intensity ratio of the sextet is expressed theoretically as a function of an angle (θ) between the γ -ray direction and the spin direction

$$3 : \frac{4 \sin^2 \theta}{1 + \cos^2 \theta} : 1 : 1 : \frac{4 \sin^2 \theta}{1 + \cos^2 \theta} : 3.$$

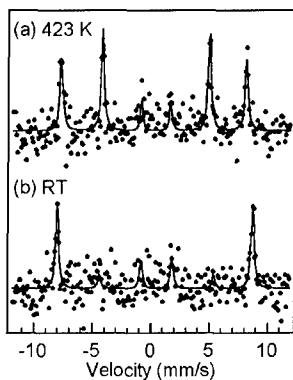


Figure 4. CEMS spectra of an $\alpha\text{-Fe}_2\text{O}_3(102)$ film deposited on $\alpha\text{-Al}_2\text{O}_3(102)$ measured at (a) 423 K and (b) room temperature.

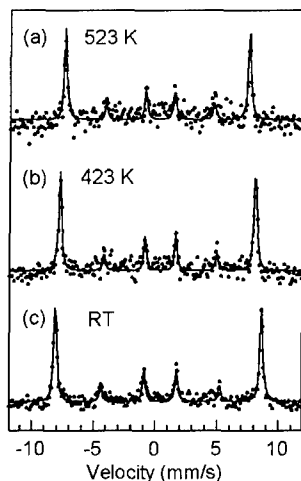


Figure 5. CEMS spectra of a $\text{CoFe}_2\text{O}_4/\alpha\text{-Fe}_2\text{O}_3$ bilayered film on $\alpha\text{-Al}_2\text{O}_3(102)$, measured at (a) 523 K, (b) 423 K, and (c) room temperature. Thicknesses of the CoFe_2O_4 and $\alpha\text{-Fe}_2\text{O}_3$ layers were 25 and 100 nm, respectively.

CEMS spectra of an $\alpha\text{-Fe}_2\text{O}_3(102)$ film without a CoFe_2O_4 covering layer are shown in fig. 4 as a function of the temperature. The spectra had the intensity ratio of nearly 3:0:1:1:0:3 at 300 K and 3:4:1:1:4:3 at 423 K. The spin axis of the $\alpha\text{-Fe}_2\text{O}_3(102)$ film was abruptly changed from the perpendicular direction ($\theta=0^\circ$) to the in-plane direction ($\theta=90^\circ$) at about 400 K.

Besides the intensity ratio of the CEMS spectra of the $\text{CoFe}_2\text{O}_4/\alpha\text{-Fe}_2\text{O}_3(102)$ bilayered film did not show any temperature dependence, even when the $\alpha\text{-Fe}_2\text{O}_3(102)$ layer was covered by a very thin, 25 nm-thick, CoFe_2O_4 layer. All spectra of the $\alpha\text{-Fe}_2\text{O}_3(102)$ base layer had the intensity ratio of about 3:0:1:1:0:3 as shown in fig. 5. The $\alpha\text{-Fe}_2\text{O}_3$ layer covered by CoFe_2O_4 did not show the spin-flip transition. The spin direction in $\alpha\text{-Fe}_2\text{O}_3$ was fixed perpendicular to the film plane over the all temperatures.

In-plane and out-of-plane magnetization curves of the $\text{CoFe}_2\text{O}_4/\alpha\text{-Fe}_2\text{O}_3$ bilayered films were also measured at various temperatures. Figs. 6(a) and (b) show room temperature magnetization curves of the 200 nm-thick CoFe_2O_4 films without and with the $\alpha\text{-Fe}_2\text{O}_3(102)$ base layers, respectively. No uniaxial magnetic anisotropy nor exchange bias field was induced in the CoFe_2O_4 layers, when they did not have the $\alpha\text{-Fe}_2\text{O}_3$ base layers. CoFe_2O_4 is known to have a large magnetocrystalline anisotropy along the $\langle 100 \rangle$ direction [8]. The (100)-oriented CoFe_2O_4 layers could have domain structures magnetized along the in-plane [100] and [010] and the out-of-plane [001] directions. The large coercivity was, thus, observed in both in-plane and out-of-plane hysteresis loops.

On the other hands, the CoFe_2O_4 layers deposited on the $\alpha\text{-Fe}_2\text{O}_3(102)$ base layers had a large in-plane magnetic anisotropy. The exchange bias field of about 200 Oe was induced. The spin

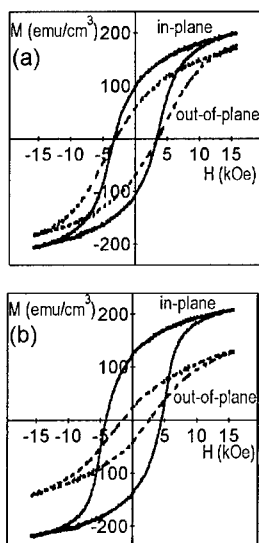


Figure 6. In-plane and out-of-plane magnetization curves of (a) a 200 nm-thick CoFe_2O_4 film deposited on $\alpha\text{-Al}_2\text{O}_3(102)$, and (b) a $\text{CoFe}_2\text{O}_4(200 \text{ nm})/\alpha\text{-Fe}_2\text{O}_3(100 \text{ nm})$ bilayered film on $\alpha\text{-Al}_2\text{O}_3(102)$. The magnetization curves were measured at room temperature

axis of the $\alpha\text{-Fe}_2\text{O}_3$ base layers was directed perpendicular to the film plane as discussed above. The magnetization of the CoFe_2O_4 (FM) layers was exactly coupled perpendicularly to the spin axis of the $\alpha\text{-Fe}_2\text{O}_3$ (AFM) layers. The 90° FM-AFM coupling observed in $\text{CoFe}_2\text{O}_4/\alpha\text{-Fe}_2\text{O}_3$ bilayered films was in good agreement with the theoretical result reported by Koon [1]. The large in-plane anisotropy of the CoFe_2O_4 layers was probably induced by the 90° coupling with the $\alpha\text{-Fe}_2\text{O}_3$ layers and it should suppress the spin-flip transition of the $\alpha\text{-Fe}_2\text{O}_3$ layers irreversibly.

SUMMARY

Exchange coupling between a ferrimagnetic CoFe_2O_4 layer and an antiferromagnetic $\alpha\text{-Fe}_2\text{O}_3$ layer was examined to prepare $\text{CoFe}_2\text{O}_4/\alpha\text{-Fe}_2\text{O}_3$ bilayered films. (100)-oriented CoFe_2O_4 layers were formed on well-crystallized epitaxial $\alpha\text{-Fe}_2\text{O}_3(102)$ layers deposited on $\alpha\text{-Al}_2\text{O}_3(102)$ single-crystalline substrates. The $\alpha\text{-Fe}_2\text{O}_3(102)$ films without CoFe_2O_4 layers clearly showed the spin-flip transition at about 400 K. The spin axis lay within the (102) plane of $\alpha\text{-Fe}_2\text{O}_3$ at high temperatures but became almost normal to the plane at low temperatures. However the $\alpha\text{-Fe}_2\text{O}_3(102)$ layers covered by CoFe_2O_4 layers did not show any spin-flip transition. The spin axis of the $\alpha\text{-Fe}_2\text{O}_3(102)$ base layers was fixed on the perpendicular to the films. Magnetic hysteresis loops of $\text{CoFe}_2\text{O}_4/\alpha\text{-Fe}_2\text{O}_3$ bilayered films indicated that a large in-plane magnetic anisotropy and an exchange bias field were induced in the films. The 90° coupling at the interface between ferrimagnetic and antiferromagnetic materials was directly observed in the $\text{CoFe}_2\text{O}_4/\alpha\text{-Fe}_2\text{O}_3$ system fabricated entirely of oxides.

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